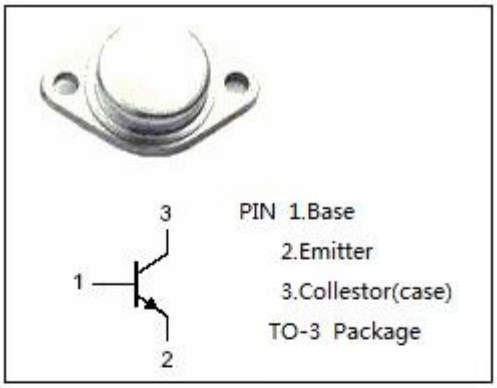
isc Silicon NPN Power Transistor 2SD556

DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= 110V (Min)
- Wide Area of Safe Operation
- High Power
- High Current Capability
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

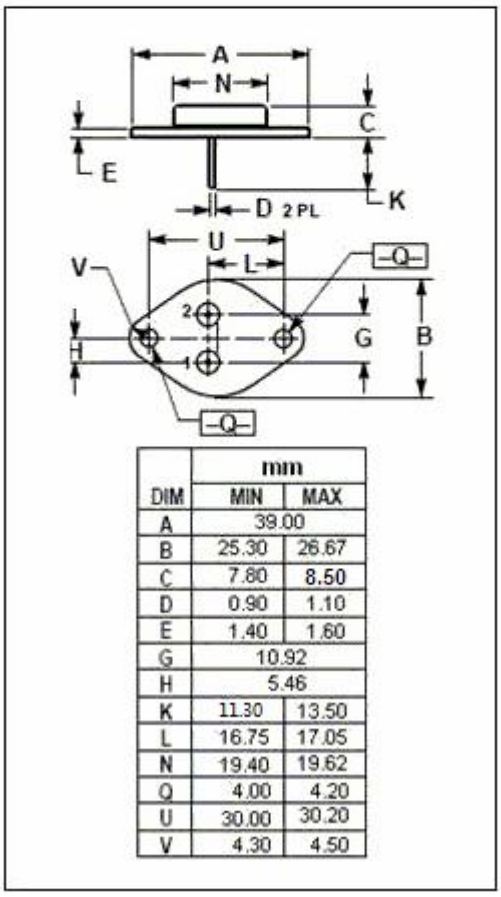


APPLICATIONS

- Designed for high power AF amplifier applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	MAX	UNIT
V_{CBO}	Collector-Base Voltage	110	V
V_{CEO}	Collector-Emitter Voltage	110	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	15	A
I_B	Base Current-Continuous	20	A
P_C	Collector Power Dissipation @T_C=25℃	120	W
T_j	Junction Temperature	175	℃
T_{stg}	Storage Temperature Range	-65~175	℃



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.30	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 10mA ; I_B= 0	110			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 1mA ; I_C= 0	6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 5A; I_B= 0.5A			1.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= 5A ; V_{CE}= 4V			1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 110V; I_E= 0			0.1	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 6V; I_C=0			0.1	mA
h_{FE-1}	DC Current Gain	I_C= 1A ; V_{CE}= 4V	60		200	
h_{FE-2}	DC Current Gain	I_C= 5A ; V_{CE}= 4V	30		120	
f_T	Current-Gain—Bandwidth Product	I_C= 0.5A;V_{CE}= 10V		8		MHz